

AMENDMENT TO THE SPECIFICATION:

Please replace the paragraph beginning on page 10, line 20 and continuing to page 11, line 9 with the following paragraph:

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According to the present embodiment, in the doping process into the semiconductor layer 4, P-type impurities are doped into the resist mask 7 simultaneously with doping into the semiconductor layer 4. However, the resist mask 7 is removed and is not present in the completed 'TFT'. In other words, immediately above the gate electrode 2, the semiconductor layer 4 and the interlayer insulating film 2-8 are in direct contact and are not separated by the ion stopper 55. In contrast to cases where the ion stopper 55 is not removed, the concentration of impurities contained in the insulating film immediately above the gate electrode 2 of the semiconductor layer 4 (that is, on the channel region 4c of the semiconductor layer 4) is less than  $10^{18}$  atoms/cc. This helps prevent occurrence of the back channel phenomenon. As a result, bottom-gate thin-film transistors with stable operational characteristics can be produced at high manufacturing yields.